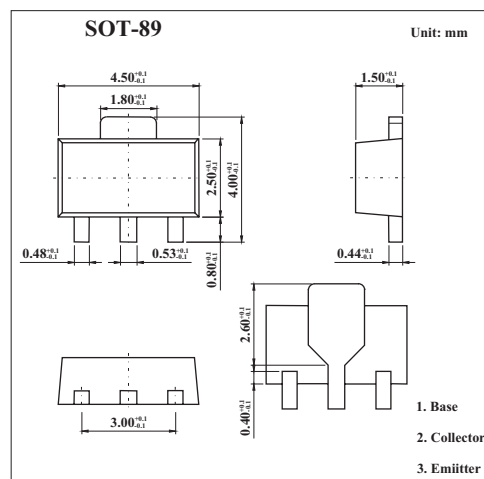


Medium Power Transistor

FCX591A

■ Features

- PNP silicon planar.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-40	V
Collector-emitter voltage	V_{CE0}	-40	V
Emitter-base voltage	V_{EB0}	-5	V
Peak pulse current	I_C	-1	A
Continuous collector current	I_{CM}	-2	A
Base current	I_B	-200	mA
Power dissipation	P_{tot}	1	W
Operating and storage temperature range	T_j, T_{stg}	-65 to +150	$^\circ\text{C}$

FCX591A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Breakdown Voltages	V(BR)CBO	IC=-100μA	-40			V
Breakdown Voltages *	V(BR)CEO	IC=-10mA	-40			V
Breakdown Voltages	V(BR)EBO	IE=-100μA	-5			V
Collector Cut-Off Current	ICBO	VCB=-30V			-100	nA
Collector-Emitter Cut-Off Current	ICES	VCE=-30V			-100	nA
Emitter Cut-Off Current	IEBO	VEB=-4V			-100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=-100mA, IB=-1mA IC=-500mA, IB=-20mA IC=-1A, IB=-100mA			-0.2 -0.35 -0.5	V
Base-emitter saturation voltage *	VBE(sat)	IC=-1A, IB=-50mA			-1.1	V
Base-Emitter Turn-on Voltage *	VBE(on)	IC=-1A, VCE=-5V			-1.0	V
Static Forward Current Transfer Ratio	hFE	IC=-1mA,	300			
		IC=-100mA*,	300		800	
		IC=-500mA*, VCE=-5V	250			
		IC=-1A*,	160			
		IC=-2A*,	30			
Transitional frequency	fT	IC=-50mA, VCE=-10V, f=100MHz	150			MHz
Output capacitance	Cobo	VCB=-10V, f=1MHz			10	pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	P2
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